



SANYO Semiconductors

## DATA SHEET

# SFT1307 — P-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Motor drive application.
- Low ON-resistance.
- 4V drive.

### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-45	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		-14	A
Drain Current (PW≤10μs)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-56	A
Allowable Power Dissipation	P <sub>D</sub>		1.0	W
		Tc=25°C	20	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-45			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-45V, V <sub>GS</sub> =0V			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-7A	7.2	12		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-7A, V <sub>GS</sub> =-10V		31	41	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-7A, V <sub>GS</sub> =-4V		45	63	mΩ

Marking : T1307

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SANYO Semiconductor Co., Ltd.

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# SFT1307

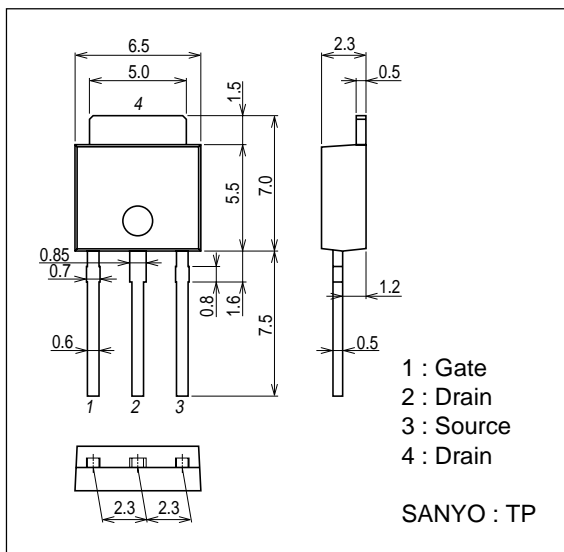
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V <sub>DS</sub> =-20V, f=1MHz		2580		pF
Output Capacitance	Coss	V <sub>DS</sub> =-20V, f=1MHz		265		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =-20V, f=1MHz		210		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		30		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		52		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		210		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		100		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-14A		46		nC
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-14A		7		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-14A		8		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-14A, V <sub>GS</sub> =0V		-0.95	-1.2	V

## Package Dimensions

unit : mm (typ)

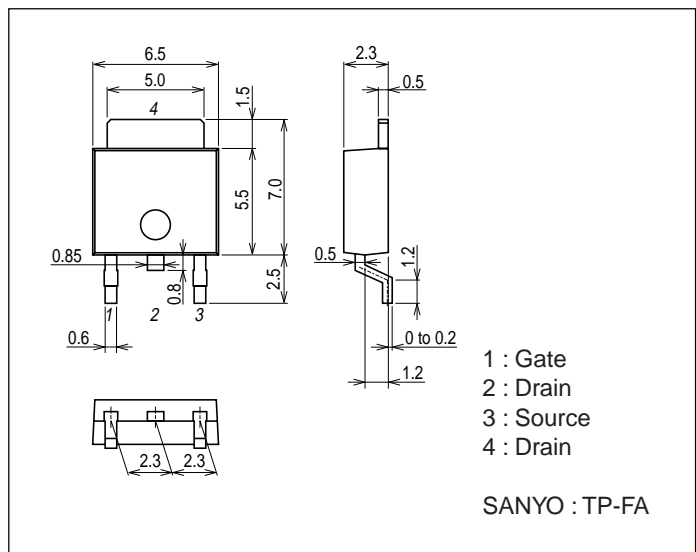
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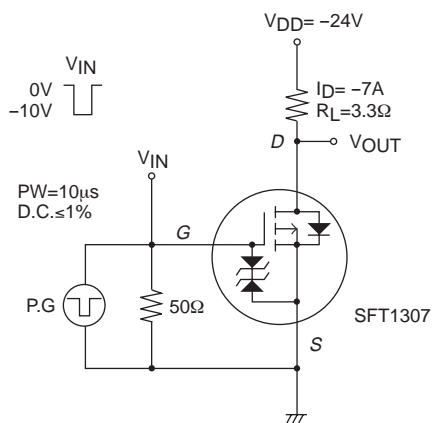
## Package Dimensions

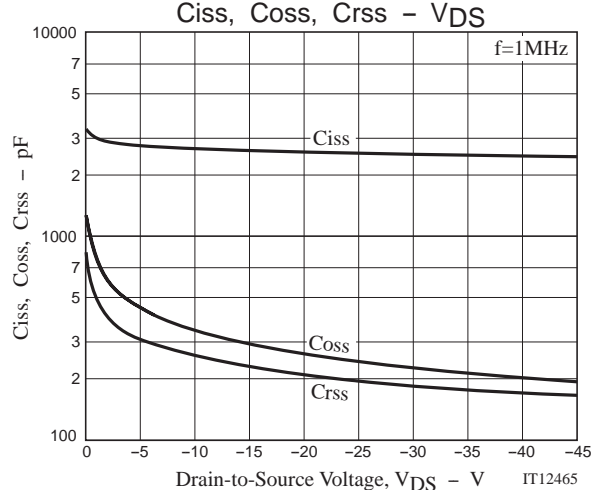
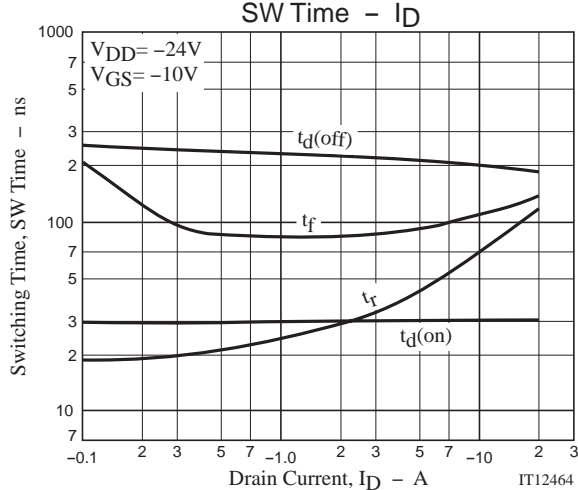
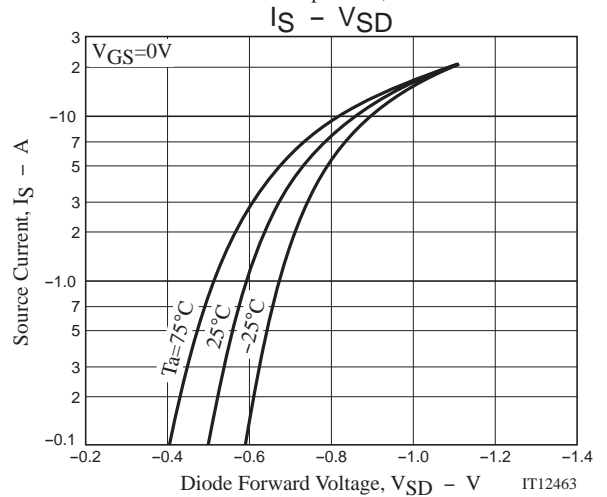
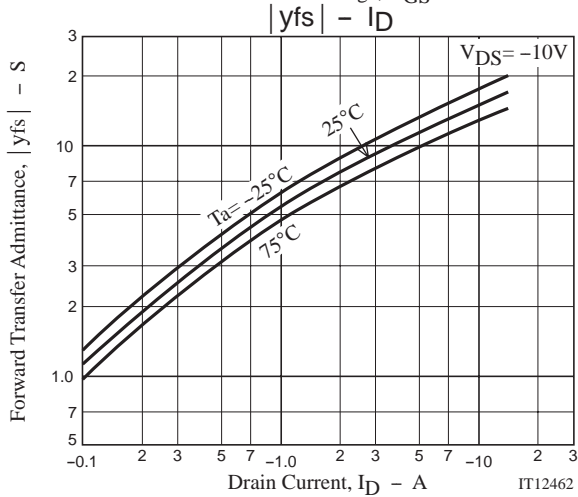
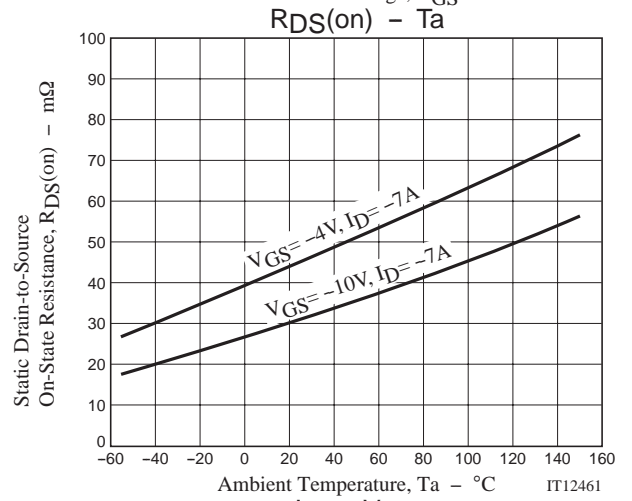
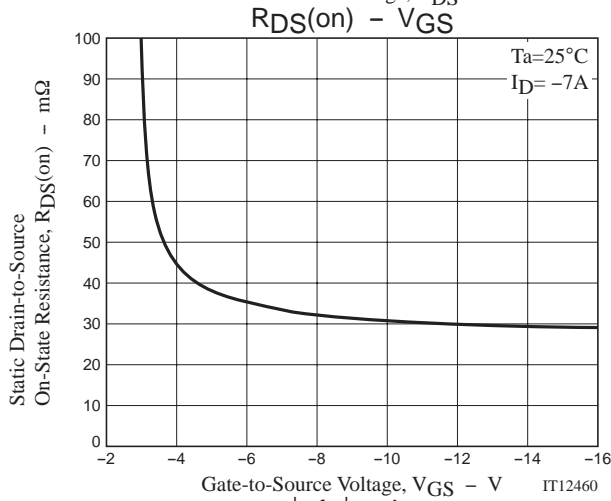
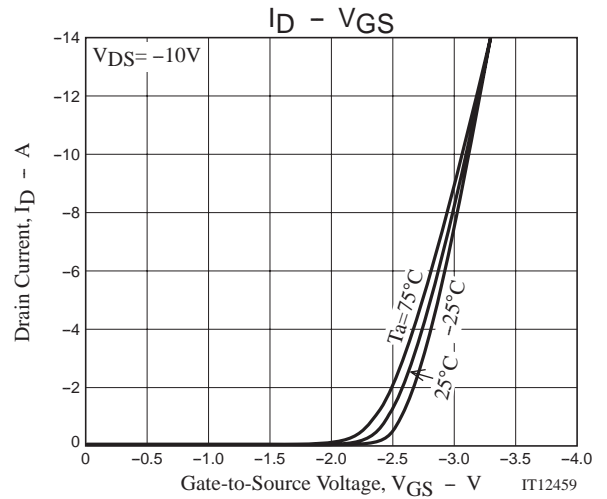
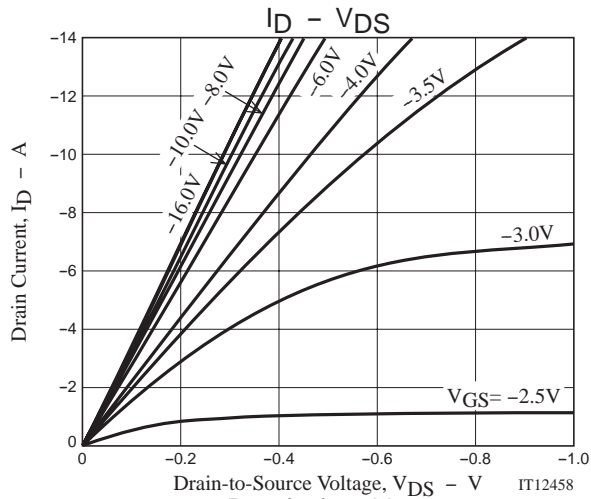
unit : mm(typ)

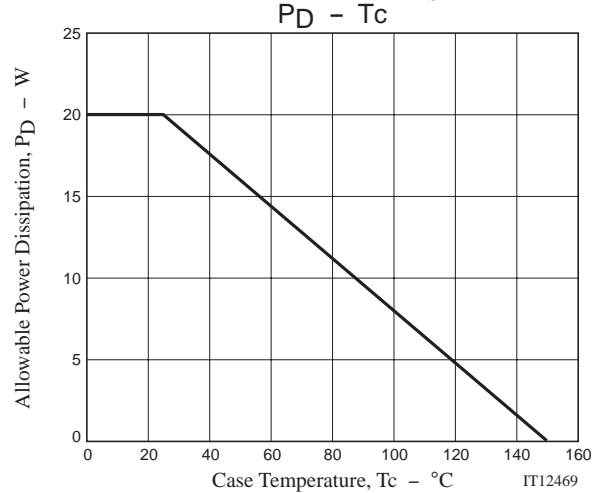
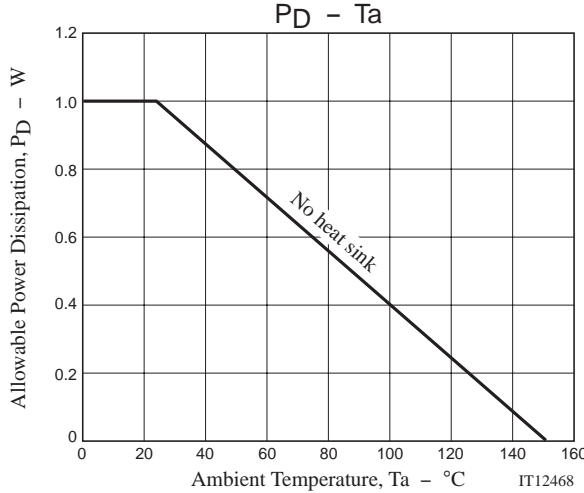
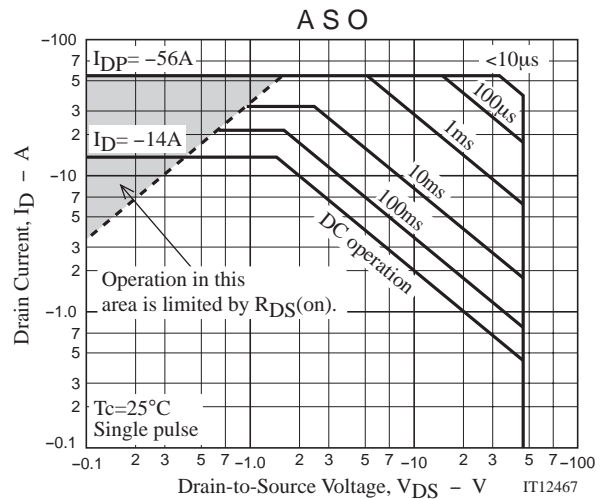
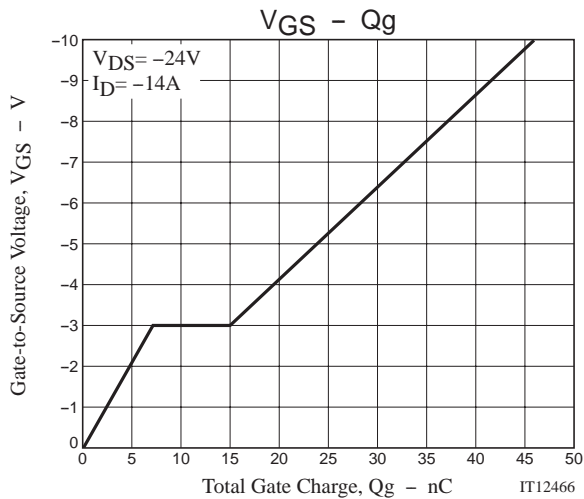
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## Switching Time Test Circuit







Note on usage : Since the SFT1307 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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